

HVGT High voltage silicon rectifier is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

SHAPE DISPLAY:



FEATURES:

1. High reliability design.
2. High voltage design.
3. High frequency design..
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High frequency switching power supply.
2. Power supply of laser equipment .
3. General purpose high voltage rectifier.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: external lead.
3. Net weight: 122 grams (approx).

SIZE: (Unit:mm)

HVGT NAME: HVC-152520

HVC-152520 Series

Screw Holes M5



MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V _{RRM}	T _a =25°C	15	kV
Average Output Current	I _F	T _a =40°C; Resistive Load	3.0	A
Surge Current	I _{FSM}	T _a =25°C; 8.3 mS; 1/2 Sine(60Hz)	60	A
Junction Temperature	T _J		-40~+125	°C
Allowable Operation Case Temperature	T _c		125	°C
Storage Temperature	T _{STG}		-40~+125	°C

ELECTRICAL CHARACTERISTICS: T_a=25°C (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V _F	at 25°C; I _F = I _{F(AV)}	18	V
Maximum Reverse Current	I _{R1}	at 25°C; V _R = V _{RRM}	5.0	uA
	I _{R2}	at 100°C; V _R = V _{RRM}	50	uA
Maximum Reverse Recovery Time	T _{RR}	at 25°C; I _F =0.5I _R ; I _R =I _{FAVM} ; I _{RR} =0.25I _R	100	nS
Junction Capacitance	C _J	at 25°C; V _R =0V; f=1MHz	--	pF

Fig 1

Forward Current Derating Curve

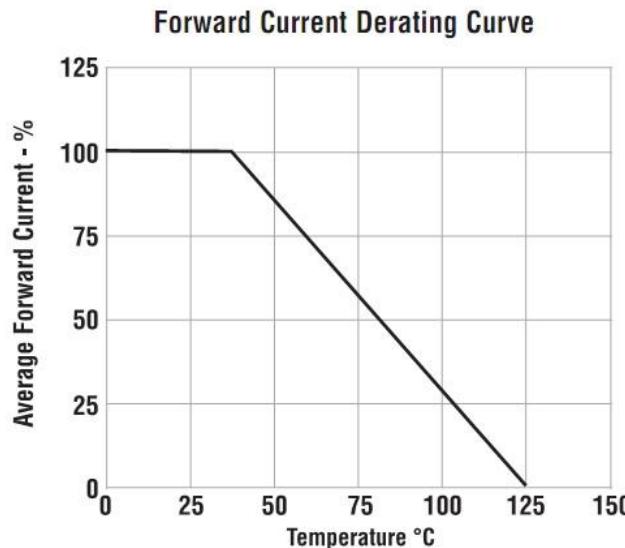
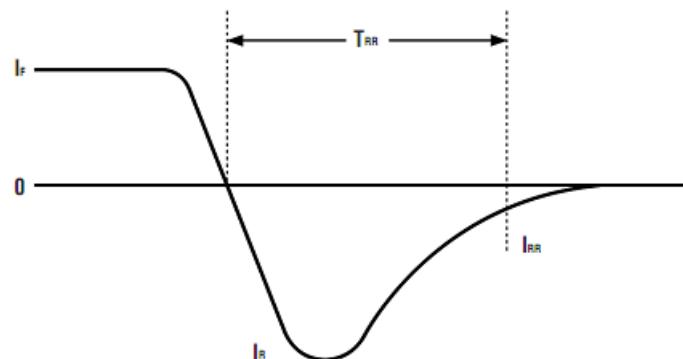


Fig 2

Reverse Recovery Measurement Waveform



Typical data capture points: $I_F = 0.5I_R$, $I_R, I_{RR} = 0.25I_R$
 I_R is typically the rated average forward current maximum (I_{FAVM}) of the D.U.T

Fig 3

Non-Repetitive Surge Current

